TOSHIBA

10JL2CZ47A

TOSHIBA HIGH EFFICIENCY DIODE STACK (HED) SILICON EPITAXIAL TYPE

0JL2CZ47A

SWITCHING TYPE POWER SUPPLY APPLICATION

CONVERTER & CHOPPER APPLICATION

Repetitive Peak Reverse Voltage : V_{RRM} = 600 V

Average Output Rectified Current : $I_0 = 10 \text{ A}$

Ultra Fast Reverse-Recovery Time : $t_{rr} = 35 \text{ ns}$ (Max.)

Low Switching Losses and Output Noise.

MAXIMUM RATINGS

| CHARACTERISTIC | SYMBOL | RATING | UNIT |
|---|--------------------|----------------|------|
| Repetitive Peak Reverse Voltage | v_{RRM} | 600 | V |
| Average Output Rectified Current | IO | 10 | A |
| Peak One Cycle Surge Forward Current (Non-Repetitive, Sine Wave) | I_{FSM} | 40 (50 Hz) | A |
| Junction Temperature | T_j | -40~150 | °C |
| Storage Temperature Range | $\mathrm{T_{stg}}$ | -40~150 | °C |
| Screw Torque | CON | 0.6 | N∙m |

Unit in mm Ø 3.2 ± 0.2 0.75±0.15 2.54±0.25 ANODE 2. ANODE 3. CATHODE **JEDEC** EIAJ TOSHIBA 12-10C1A

Weight: 2.0 g

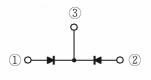
TE WWW.D. ELECTRICAL CHARACTERISTICS (Ta = 25°C)

| CHARACTERISTIC | SYMBOL | TEST CONDITION | MIN. | TYP. | MAX. | UNIT |
|--|-----------------------|--------------------------------------|------|---------|------|----------------|
| Peak Forward Voltage (Note 1) | $V_{	extbf{FM}}$ | $I_{FM} = 5 A$ | - 40 | 7 | 4.0 | V |
| Repetitive Peak Reverse Current (Note 1) | I_{RRM} | $V_{RRM} = 600 V$ | | 61 At 1 | 50 | μ A |
| Reverse Recovery Time (Note 1) | trr | $I_F = 2 A, di / dt = -20 A / \mu s$ | _ | _ | 35 | ns |
| Forward Recovery Time (Note 1) | t_{fr} | $I_{\mathbf{F}} = 1 \text{ A}$ | _ | _ | 150 | ns |
| Thermal Resistance | R _{th (j-c)} | DC Total, Junction to Case | _ | _ | 3.6 | °C/W |

(Note 1) A value of one cell.

POLARITY

MARKING





| | *1 | MARK | 10JL2CZ | TYPE | 10JL2CZ47A | | |
|---|----|-------|---|------|------------|--|--|
| | *2 | A | | PE W | DZSU. | | |
| 0 | *3 | ———Mo | Lot Number ——Month (Starting from Alphabet A) ——Year (Last Number of the Christian Era) | | | | |

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